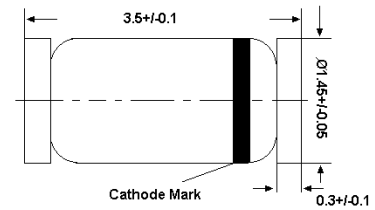


# RLZTE-11 Series

## Silicon Epitaxial Planar Zener Diodes

in MiniMELF case especially for automatic insertion.  
 The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.

LL-34



Glass case MiniMELF  
 Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Power Dissipation	$P_{\text{tot}}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	- 55 to + 175	$^\circ\text{C}$

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	$R_{\text{thA}}$	0.3 <sup>1)</sup>	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	1	V

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature

# RLZTE-11 Series

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Type	Zener Voltage Range <sup>1)</sup>			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	$V_{Znom}$	$V_{ZT}$	at $I_{ZT}$	$Z_{ZT}$	$Z_{ZK}$	at $I_{ZK}$	$T_a = 25\text{ }^\circ\text{C}$	$T_a = 125\text{ }^\circ\text{C}$	at $V_R$	
	(V)	(V)	(mA)	Max. ( $\Omega$ )	Max. ( $\Omega$ )	(mA)	Max. ( $\mu\text{A}$ )	Max. ( $\mu\text{A}$ )	(V)	
RLZTE-111.0B	0.75	0.7...0.8	5	8	50	1	-	-	-	-0.26...-0.23
RLZTE-112.0B	2	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
RLZTE-112.2B	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
RLZTE-112.4B	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
RLZTE-112.7B	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
RLZTE-113.0B	3	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
RLZTE-113.3B	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
RLZTE-113.6B	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
RLZTE-113.9B	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
RLZTE-114.3B	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
RLZTE-114.7B	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
RLZTE-115.1B	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
RLZTE-115.6B	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
RLZTE-116.2B	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
RLZTE-116.8B	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
RLZTE-117.5B	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
RLZTE-118.2B	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
RLZTE-119.1B	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
RLZTE-1110B	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
RLZTE-1111B	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
RLZTE-1112B	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
RLZTE-1113B	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
RLZTE-1115B	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
RLZTE-1116B	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
RLZTE-1118B	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
RLZTE-1120B	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
RLZTE-1122B	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
RLZTE-1124B	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
RLZTE-1127B	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
RLZTE-1130B	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
RLZTE-1133B	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
RLZTE-1136B	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
RLZTE-1139B	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
RLZTE-1143B	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
RLZTE-1147B	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
RLZTE-1151B	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
RLZTE-1156B	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
RLZTE-1162B	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
RLZTE-1168B	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
RLZTE-1175B	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

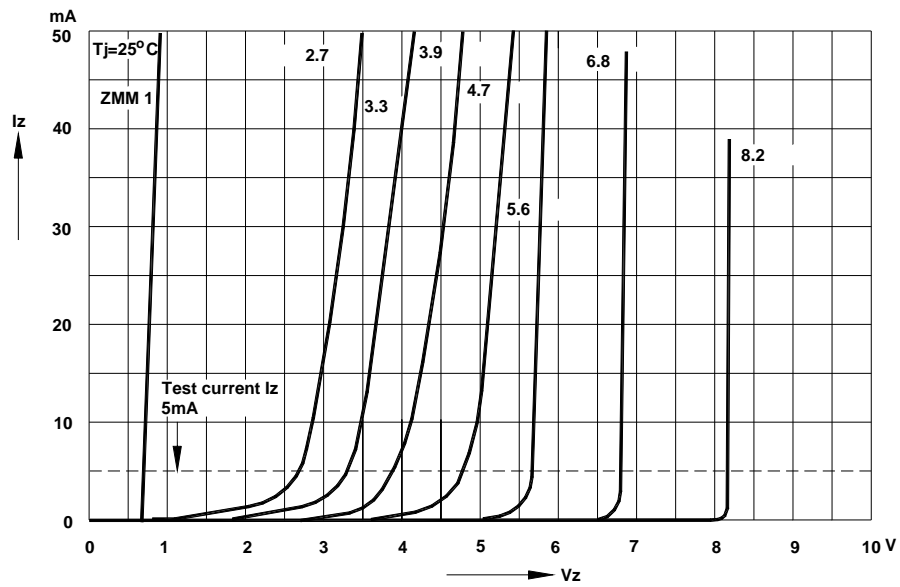
<sup>1)</sup> Tested with pulses  $t_p = 20\text{ ms}$ .

<sup>2)</sup> The ZMM1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.

# RLZTE-11 Series

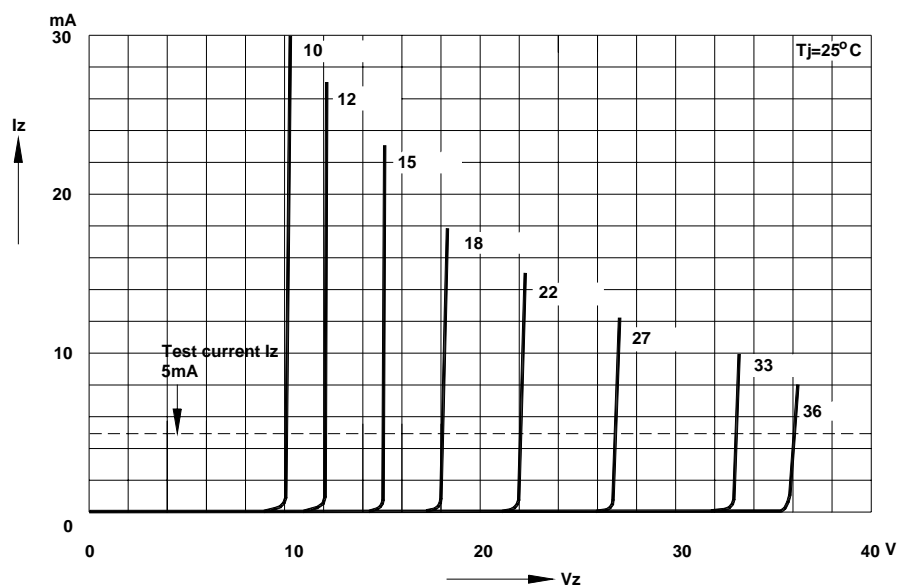
## Breakdown characteristics

$T_j = \text{constant (pulsed)}$



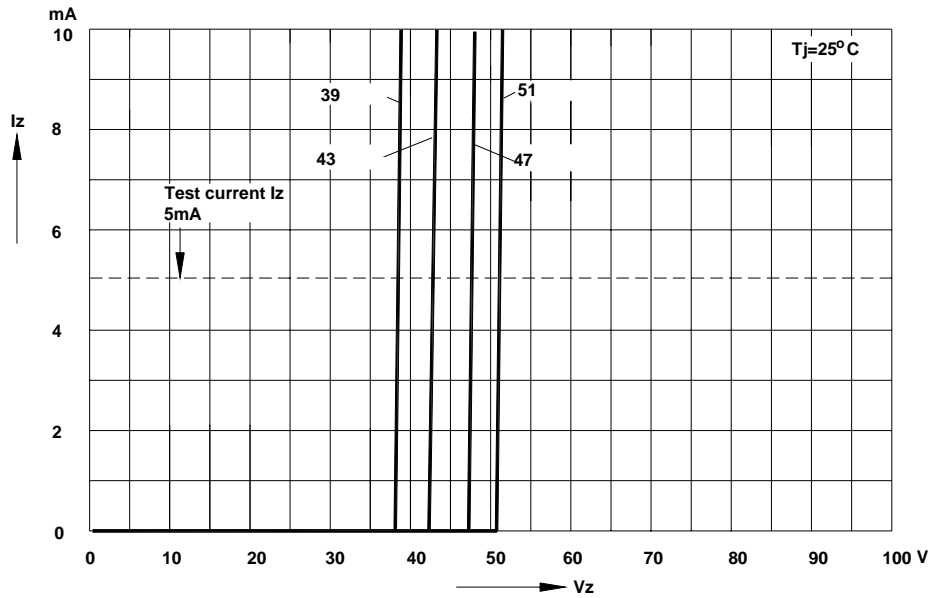
## Breakdown characteristics

$T_j = \text{constant (pulsed)}$

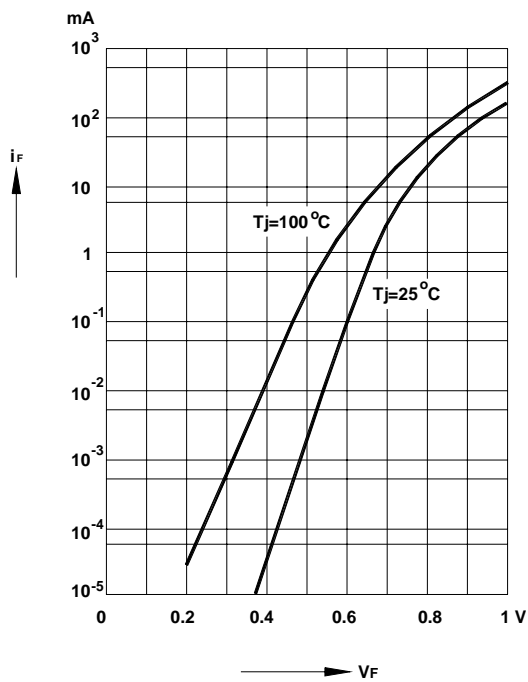


# RLZTE-11 Series

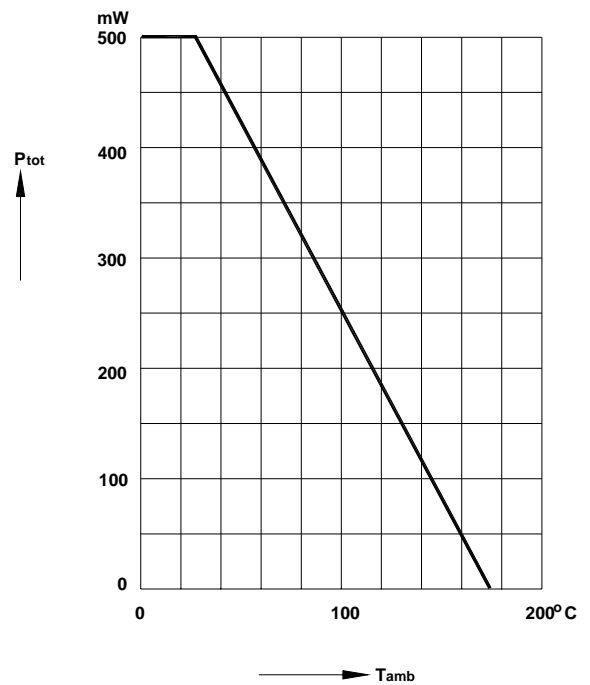
**Breakdown characteristics**  
 $T_j = \text{constant (pulsed)}$



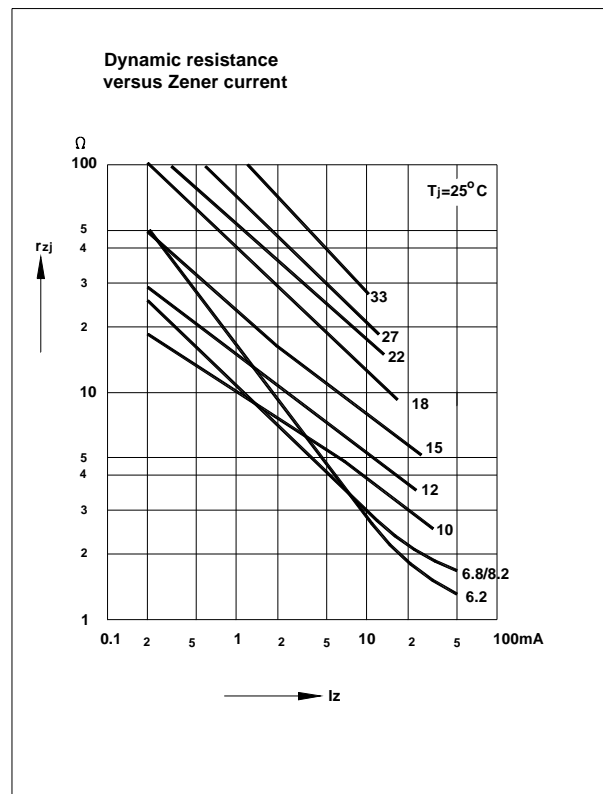
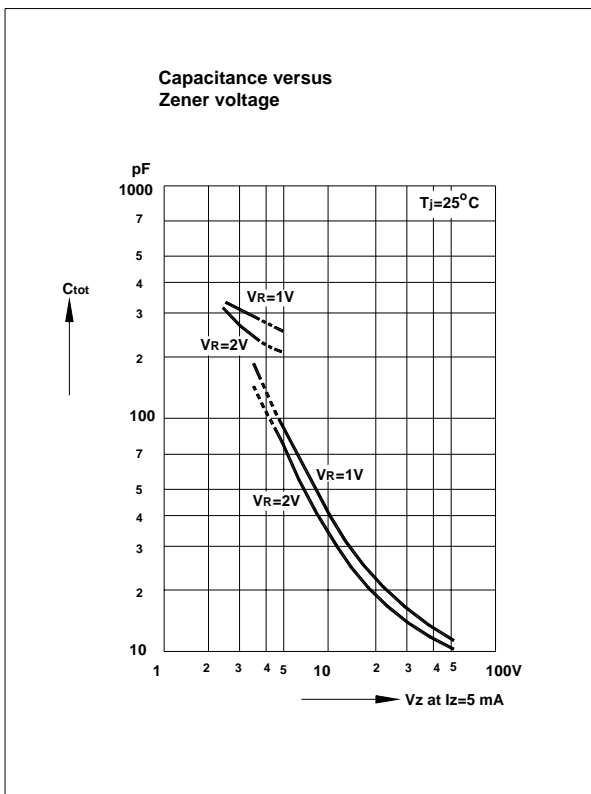
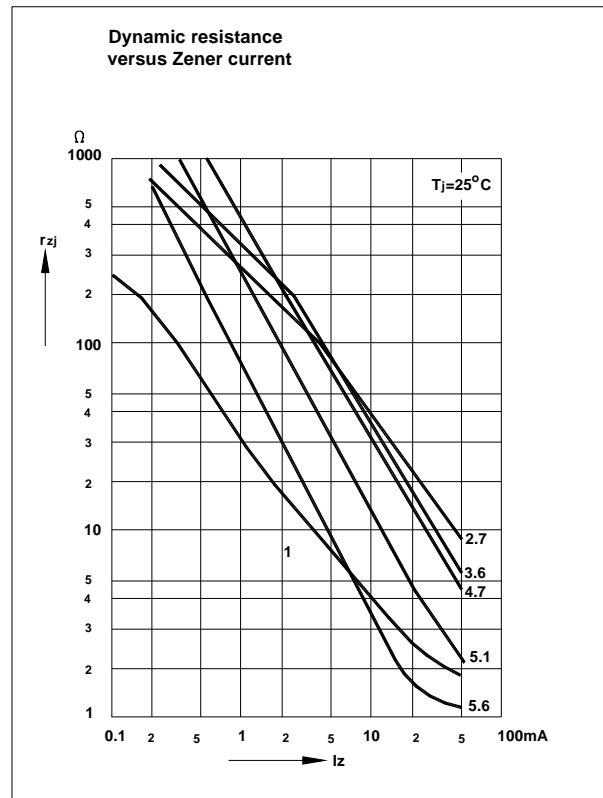
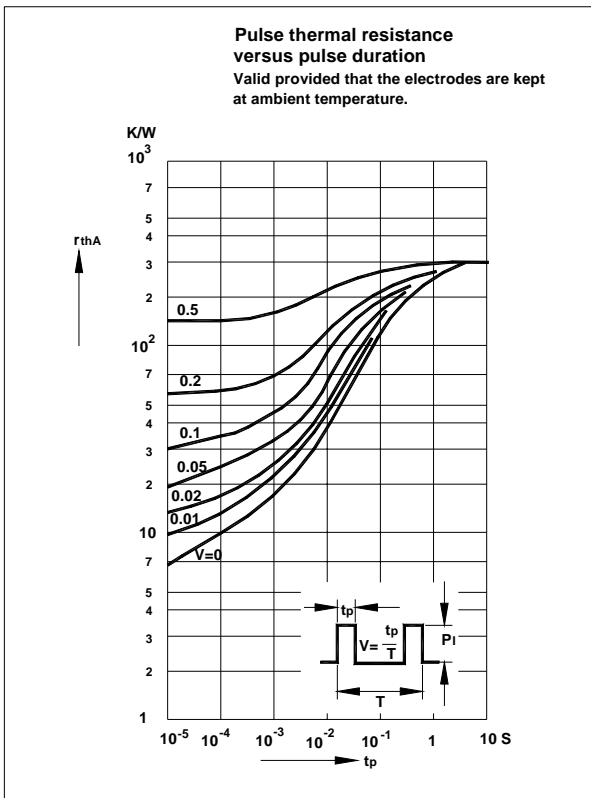
**Forward characteristics**



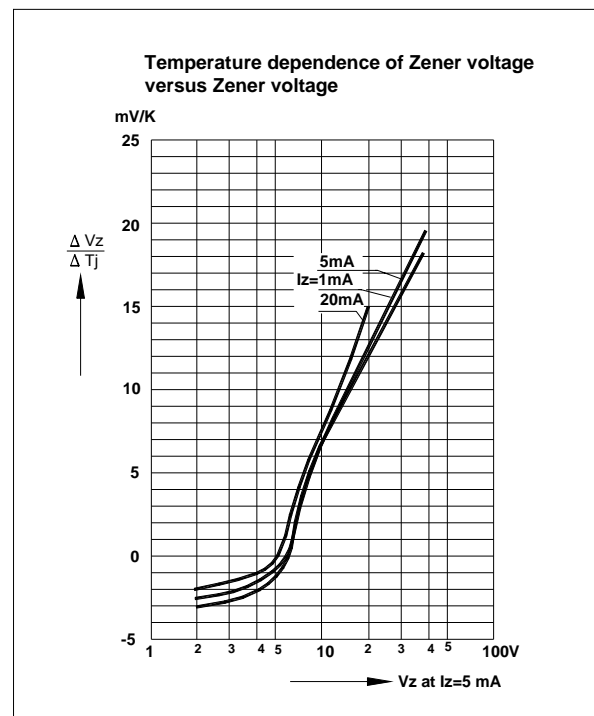
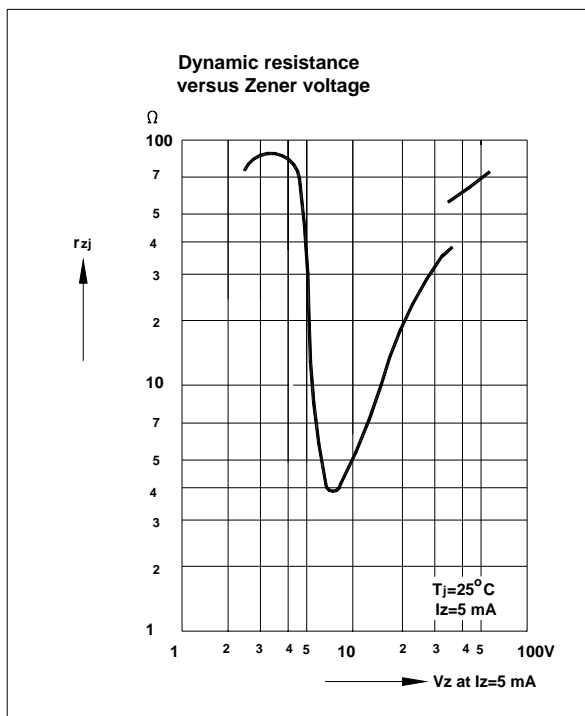
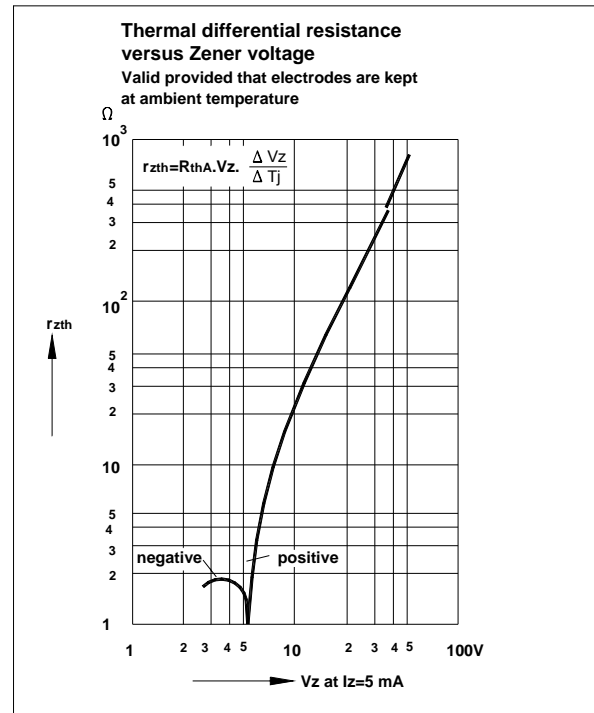
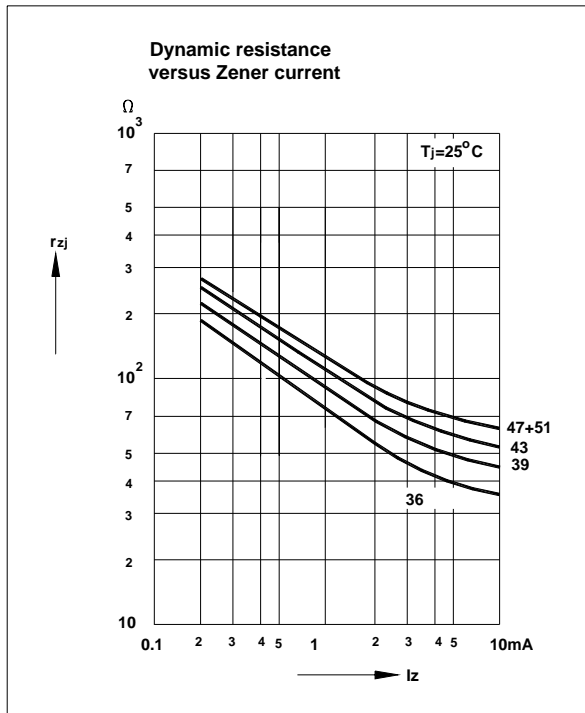
**Admissible power dissipation versus ambient temperature**  
 Valid provided that electrodes are kept at ambient temperature.



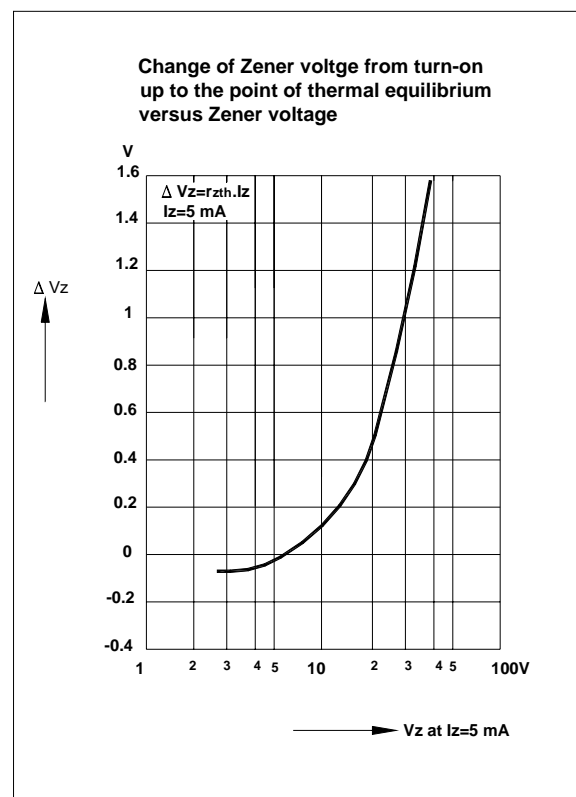
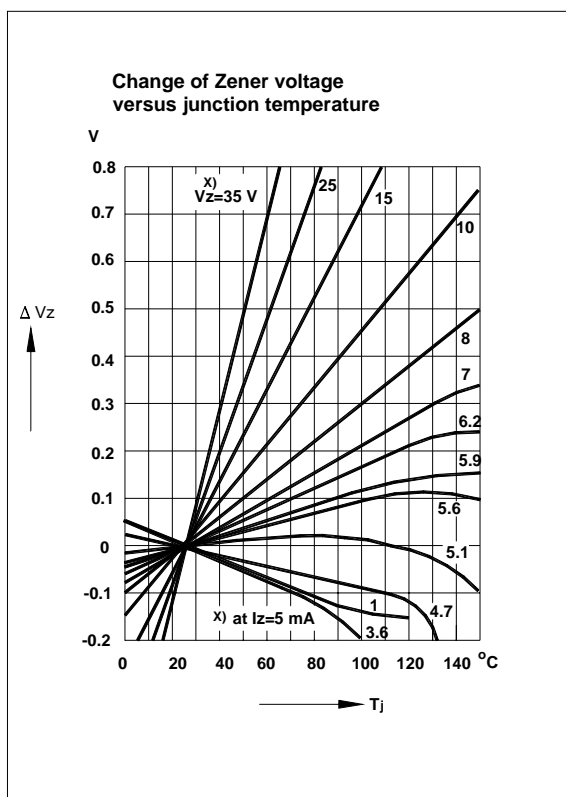
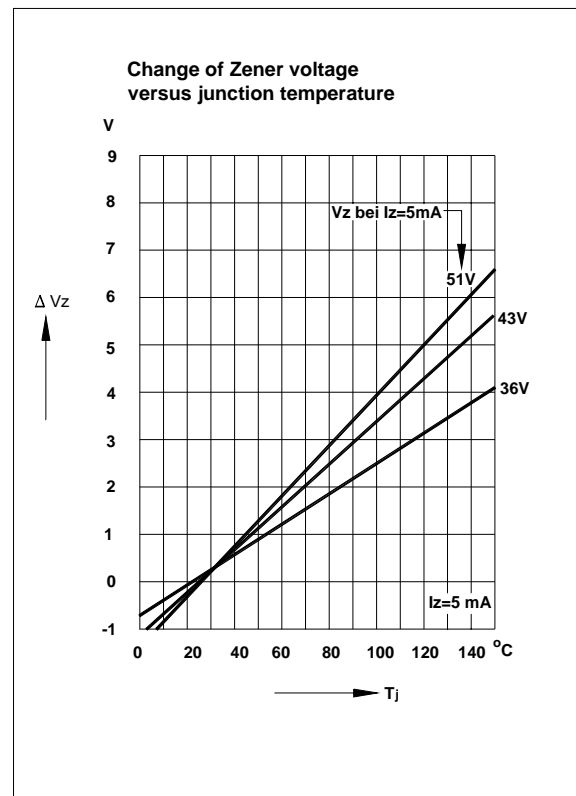
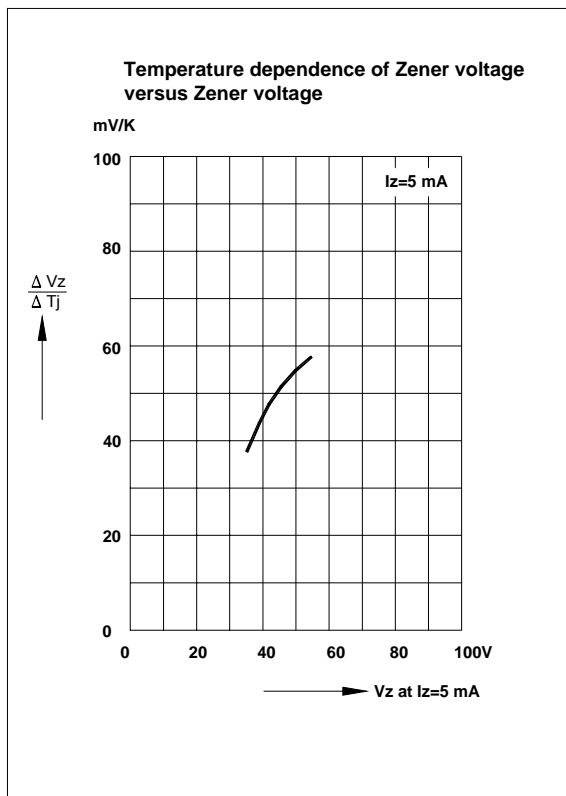
# RLZTE-11 Series



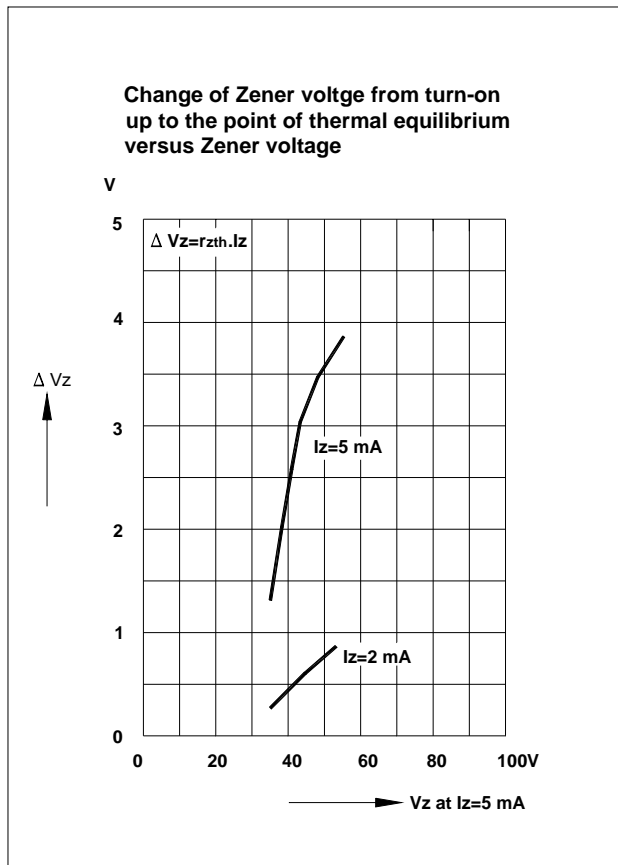
# RLZTE-11 Series



# RLZTE-11 Series



# RLZTE-11 Series





单击下面可查看定价，库存，交付和生命周期等信息

[>>YONGYUTAI\(永裕泰\)](#)